HM62V8100I Series

Wide Temperature Range Version

8 M SRAM (1024-kword × 8-bit)

ADE-203-1278B (Z)
Rev.2.00
Nov.02.2009

Description

The HM62V8100I Series is 8-Mbit static RAM organized 1,048,576-word × 8-bit. HM62V8100I Series has realized higher density, higher performance and low power consumption by employing Hi-CMOS process technology. It offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is packaged package with 0.75 mm bump pitch or standard 44-pin TSOP II for high density surface mounting.

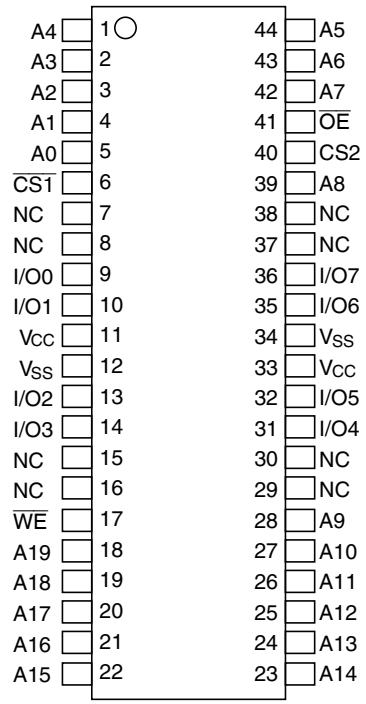
Features

- Single 3.0 V supply: 2.7 V to 3.6 V
- Fast access time: 55 ns (Max)
- Power dissipation:
  - Active: 6.0 mW/MHz (Typ)
  - Standby: 1.5 µW (Typ)
- Completely static memory.
  - No clock or timing strobe required
- Equal access and cycle times
- Common data input and output.
  - Three state output
- Battery backup operation.
  - 2 chip selection for battery backup
- Temperature range: –40 to +85°C

Ordering Information

Type No.	Access time	Package
HM62V8100LTTI-5	55 ns	400-mil 44pin plastic TSOP II (normal-bend type) (TTP-44DE)
HM62V8100LTTI-5SL	55 ns	

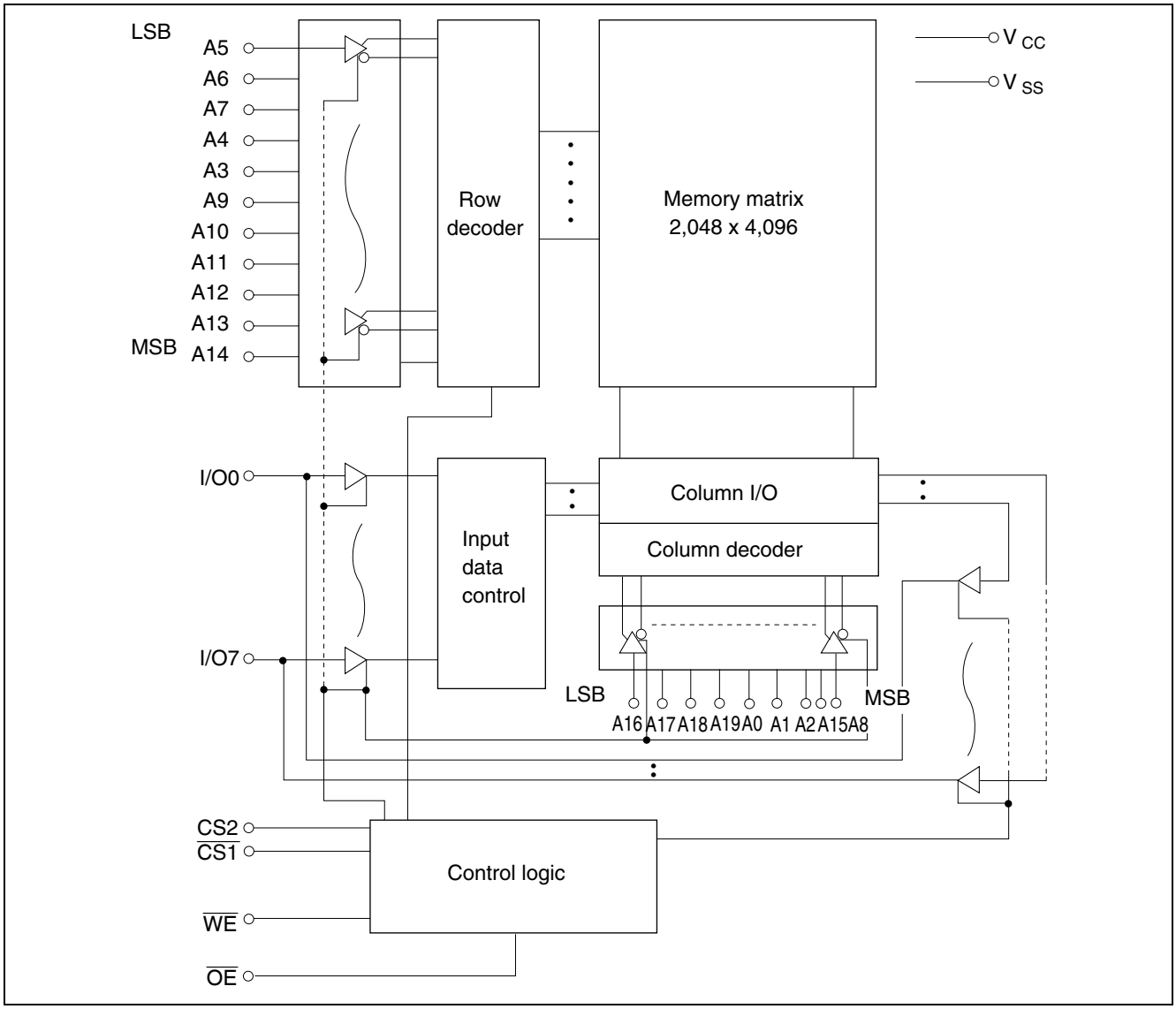
Pin Arrangement



Pin Description

Pin name	Function
A0 to A19	Address input
I/O0 to I/O7	Data input/output
$\overline{CS1}$	Chip select 1
CS2	Chip select 2
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
V_{cc}	Power supply
V_{ss}	Ground
NC	No connection

Block Diagram



Operation Table

$\overline{CS1}$	CS2	$\overline{WE}$	$\overline{OE}$	I/O0 to I/O7	Operation
H	×	×	×	High-Z	Standby
×	L	×	×	High-Z	Standby
L	H	H	L	Dout	Read
L	H	L	×	Din	Write
L	H	H	H	High-Z	Output disable

Note: H: V_{IH}, L: V_{IL}, ×: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V_{SS}	V_{CC}	–0.5 to + 4.6	V
Terminal voltage on any pin relative to V_{SS}	V_T	–0.5*[1] to V_{CC} + 0.3*[2]	V
Power dissipation	P_T	1.0	W
Storage temperature range	Tstg	–55 to +125	°C
Storage temperature range under bias	Tbias	–40 to +85	°C

Notes: 1. V_T min: –3.0 V for pulse half-width ≤ 30 ns.
2. Maximum voltage is +4.6 V.

DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	V_{CC}	2.7	3.0	3.6	V	
	V_{SS}	0	0	0	V	
Input high voltage	V_{IH}	2.2	—	V_{CC} + 0.3	V	
Input low voltage	V_{IL}	–0.3	—	0.6	V	1
Ambient temperature range	Ta	–40	—	85	°C	

Note: 1. V_{IL} min: –3.0 V for pulse half-width ≤ 30 ns.

DC Characteri stics

Parameter	Symbol	Min	Typ*1	Max	Unit	Test conditions
Input leakage current	$\|I_{LI}\|$	—	—	1	µA	Vin = V_{SS} to V_{CC}
Output leakage current	$\|I_{LO}\|$	—	—	1	µA	$\overline{CS1}$ = V_{IH} or CS2 = V_{IL} or $\overline{OE}$ = V_{IH} or $\overline{WE}$ = V_{IL}, or $V_{I/O}$ = V_{SS} to V_{CC}
Operating current	I_{CC}	—	—	20	mA	$\overline{CS1}$ = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/V_{IL}, $I_{I/O}$ = 0 mA
Average operating current	I_{CC1}	—	14	25	mA	Min. cycle, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS1}$ = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/V_{IL}
	I_{CC2}	—	2	4	mA	Cycle time = 1 µs, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS1}$ ≤ 0.2 V, CS2 ≥ V_{CC} – 0.2 V V_{IH} ≥ V_{CC} – 0.2 V, V_{IL} ≤ 0.2 V
Standby current	I_{SB}	—	0.1	0.3	mA	CS2 = V_{IL}
Standby current	I_{SB1}*2	—	0.5	25	µA	0 V ≤ Vin (1) 0 V ≤ CS2 ≤ 0.2 V or (2) $\overline{CS1}$ ≥ V_{CC} – 0.2 V, CS2 ≥ V_{CC} – 0.2 V
	I_{SB1}*3	—	0.5	10	µA	
Output high voltage	V_{OH}	2.2	—	—	V	I_{OH} = –1 mA
Output low voltage	V_{OL}	—	—	0.4	V	I_{OL} = 2 mA

Note: 1. Typical values are at V_{CC} = 3.0 V, Ta = +25°C and not guaranteed.
2. This characteristic is guaranteed only for L version.
3. This characteristic is guaranteed only for L-SL version.

Capacitance (Ta = +25°C, f = 1.0 MHz)

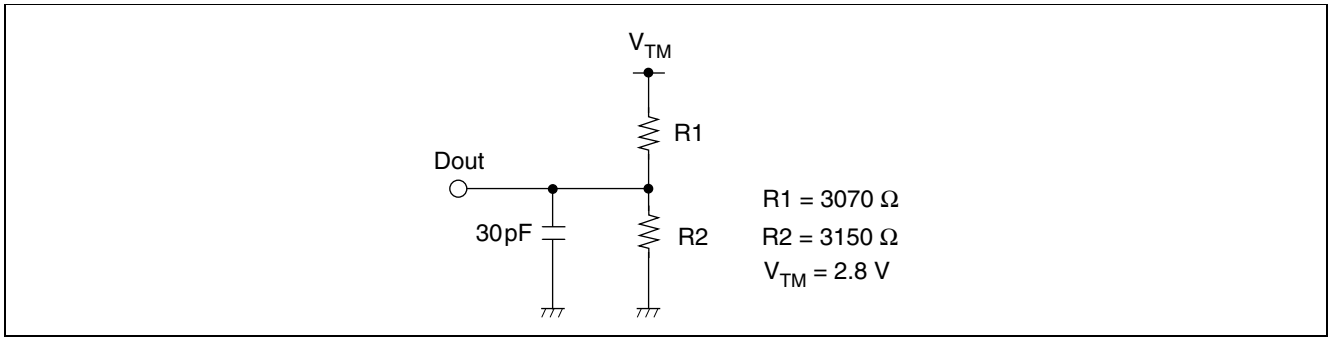
Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	Note
Input capacitance	Cin	—	—	8	pF	Vin = 0 V	1
Input/output capacitance	$C_{I/O}$	—	—	10	pF	$V_{I/O}$ = 0 V	1

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics (Ta = -40 to +85°C, VCC = 2.7 V to 3.6 V, unless otherwise noted.)

Test Conditions

- Input pulse levels: V_{IL} = 0.4 V, V_{IH} = 2.2 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figures (Including scope and jig)



Read Cycle

		HM62V8100I			
		-5			
Parameter	**Symbol**	**Min**	**Max**	**Unit**	**Notes**
Read cycle time	t_{RC}	55	—	ns	
Address access time	t_{AA}	—	55	ns	
Chip select access time	t_{ACS1}	—	55	ns	
	t_{ACS2}	—	55	ns	
Output enable to output valid	t_{OE}	—	35	ns	
Output hold from address change	t_{OH}	10	—	ns	
Chip select to output in low-Z	t_{CLZ1}	10	—	ns	2, 3
	t_{CLZ2}	10	—	ns	2, 3
Output enable to output in low-Z	t_{OLZ}	5	—	ns	2, 3
Chip deselect to output in high-Z	t_{CHZ1}	0	20	ns	1, 2, 3
	t_{CHZ2}	0	20	ns	1, 2, 3
Output disable to output in high-Z	t_{OHZ}	0	20	ns	1, 2, 3

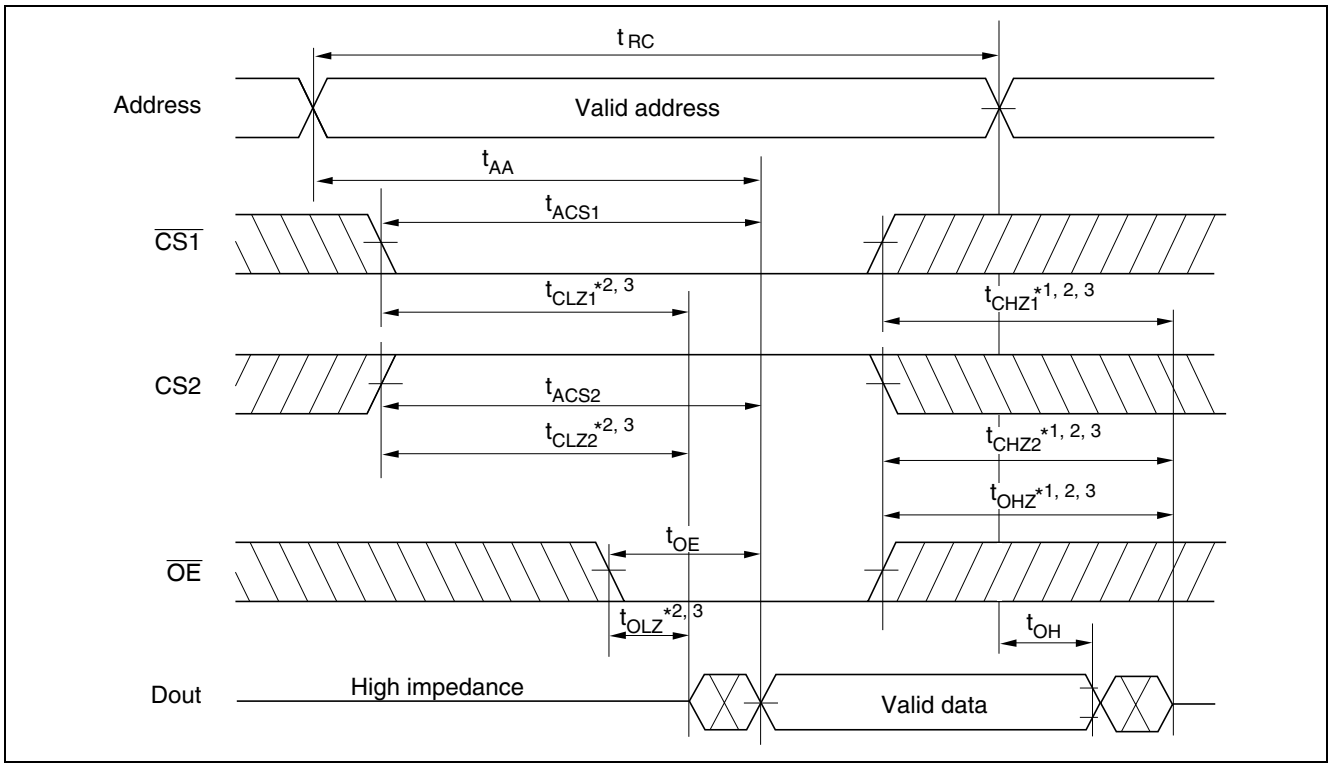
Write Cycle

		HM62V8100I			
		-5			
Parameter	**Symbol**	**Min**	**Max**	**Unit**	**Notes**
Write cycle time	t_{WC}	55	—	ns	
Address valid to end of write	t_{AW}	50	—	ns	
Chip selection to end of write	t_{CW}	50	—	ns	5
Write pulse width	t_{WP}	40	—	ns	4
Address setup time	t_{AS}	0	—	ns	6
Write recovery time	t_{WR}	0	—	ns	7
Data to write time overlap	t_{DW}	25	—	ns	
Data hold from write time	t_{DH}	0	—	ns	
Output active from end of write	t_{OW}	5	—	ns	2
Output disable to output in High-Z	t_{OHZ}	0	20	ns	1, 2
Write to output in high-Z	t_{WHZ}	0	20	ns	1, 2

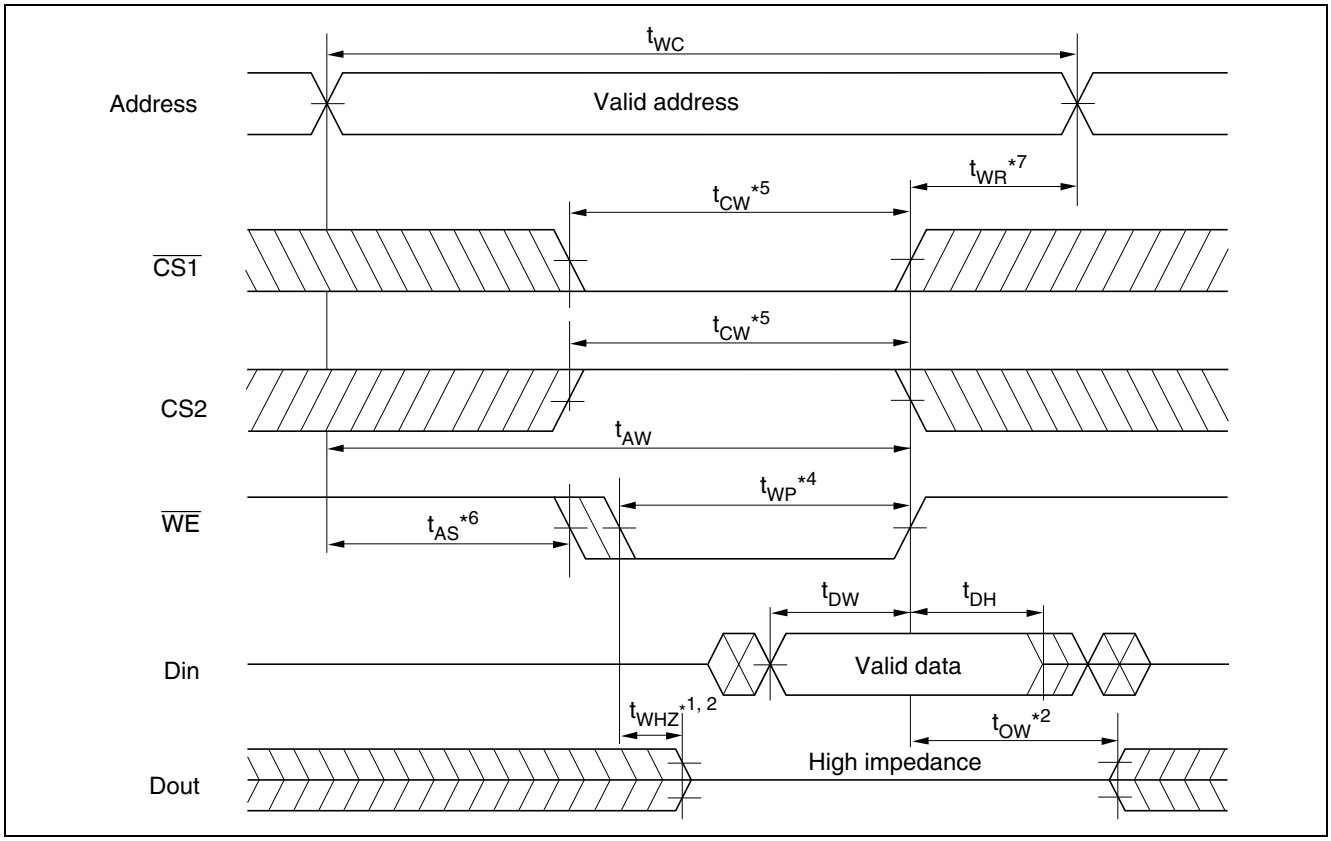
Notes:
1. t_{CHZ}, t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
2. This parameter is sampled and not 100% tested.
3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
4. A write occures during the overlap of a low $\overline{CS1}$, a high CS2, a low $\overline{WE}$. A write begins at the latest transition among $\overline{CS1}$ going low, CS2 going high, $\overline{WE}$ going low. A write ends at the earliest transition among $\overline{CS1}$ going high, CS2 going low, $\overline{WE}$ going high. t_{WP} is measured from the beginning of write to the end of write.
5. t_{CW} is measured from the later of $\overline{CS1}$ going low or CS2 going high to the end of write.
6. t_{AS} is measured from the address valid to the beginning of write.
7. t_{WR} is measured from the earliest of $\overline{CS1}$ or $\overline{WE}$ going high or CS2 going low to the end of write cycle.

Timing Waveform

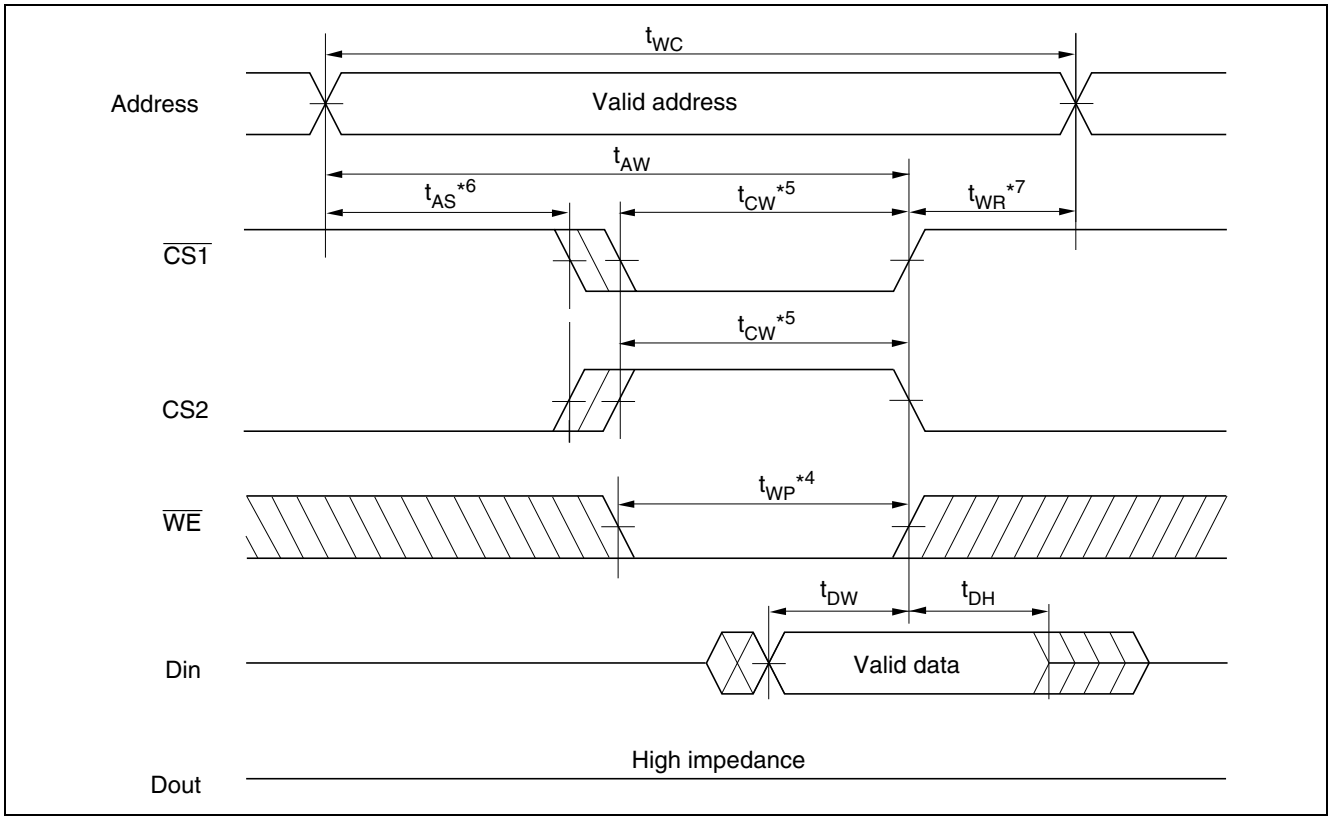
Read Cycle



Write Cycle (1) ($\overline{WE}$ Clock)



Write Cycle (2) (CS Clock, $\overline{OE}$ = VIH)

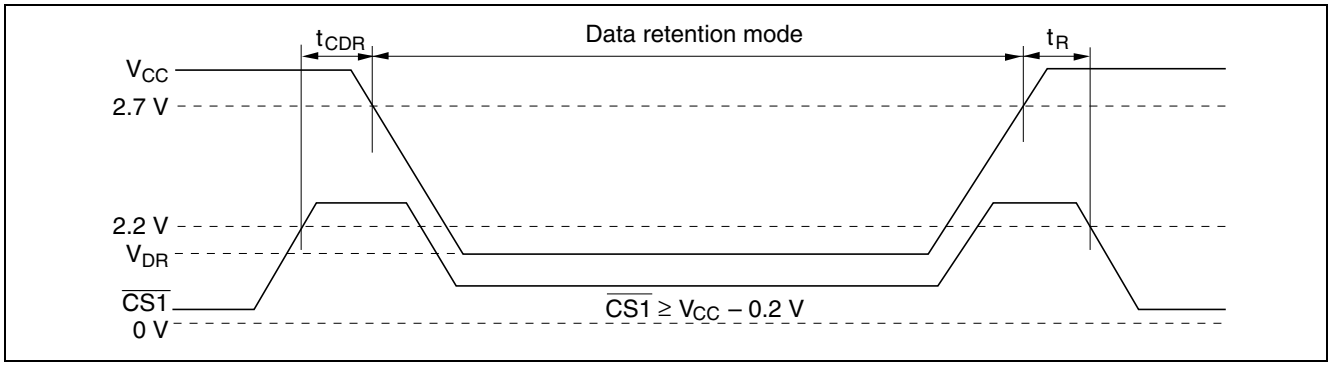


Low VCC Data Retention Characteristics (Ta = -40 to +85°C)

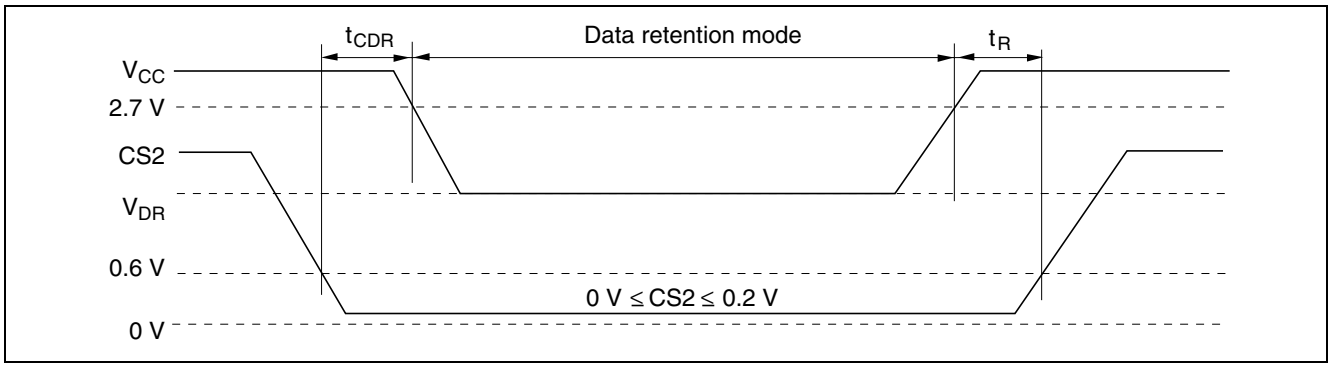
Parameter	Symbol	Min	Typ*4	Max	Unit	Test conditions*3
V_{CC} for data retention	V_{DR}	2.0	—	3.6	V	Vin ≥ 0V (1) 0 V ≤ CS2 ≤ 0.2 V or (2) CS2 ≥ V_{CC} – 0.2 V $\overline{CS1}$ ≥ V_{CC} – 0.2 V
Data retention current	I_{CCDR}*1	—	0.5	25	µA	V_{CC} = 3.0 V, Vin ≥ 0V (1) 0 V ≤ CS2 ≤ 0.2 V or (2) CS2 ≥ V_{CC} – 0.2 V, $\overline{CS1}$ ≥ V_{CC} – 0.2 V
	I_{CCDR}*2	—	0.5	10	µA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t_R	t_{RC}*5	—	—	ns	

Notes: 1. This characteristic is guaranteed only for L version.
2. This characteristic is guaranteed only for L-SL version.
3. CS2 controls address buffer, $\overline{WE}$ buffer, $\overline{CS1}$ buffer, $\overline{OE}$ buffer and Din buffer. If CS2 controls data retention mode, Vin levels (address, $\overline{WE}$, $\overline{OE}$, $\overline{CS1}$, I/O) can be in the high impedance state. If $\overline{CS1}$ controls data retention mode, CS2 must be CS2 ≥ V_{CC} – 0.2 V or 0 V ≤ CS2 ≤ 0.2 V. The other input levels (address, $\overline{WE}$, $\overline{OE}$, I/O) can be in the high impedance state.
4. Typical values are at V_{CC} = 3.0 V, Ta = +25°C and not guaranteed.
5. t_{RC} = read cycle time.

Low VCC Data Retention Timing Waveform (1) ($\overline{CS1}$ Controlled)



Low VCC Data Retention Timing Waveform (2) (CS2 Controlled)

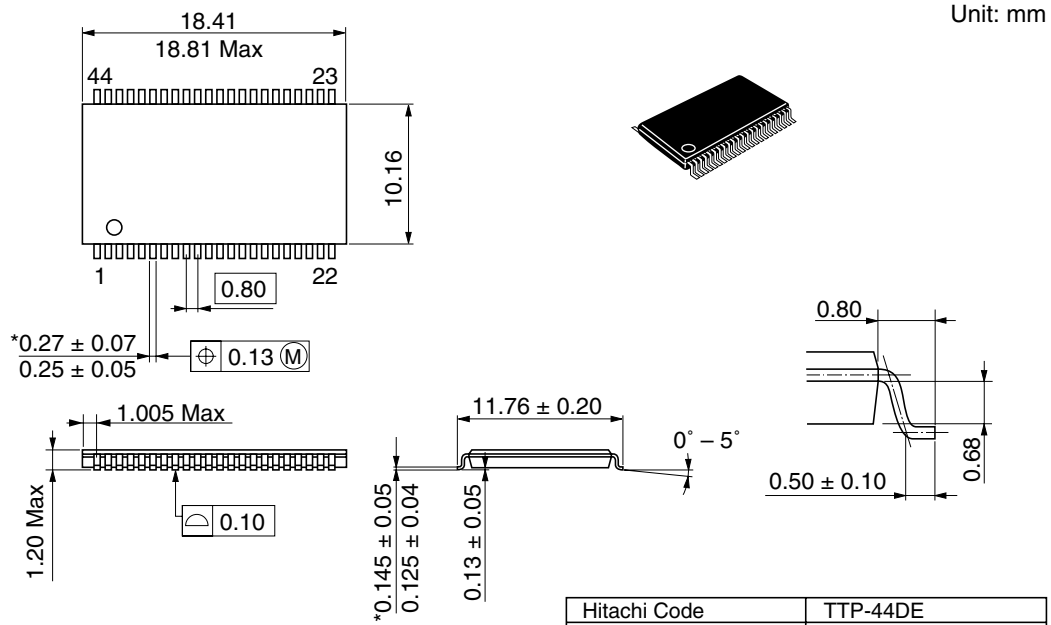


Package Dimensions

HM62V8100LTTI Series (TTP-44DE)

As of July, 2001

Unit: mm



Hitachi Code	TTP-44DE
JEDEC	—
JEITA	—
Mass (reference value)	0.43 g

*Dimension including the plating thickness
Base material dimension

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

RENESAS SALES OFFICES

http://www.renesas.com

Refer to "**http://www.renesas.com/en/network**" for the latest and detailed information.

Renesas Technology America, Inc.
450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120
Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd.
10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.
Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510

Colophon .7.2